

**BUL310**

## HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- STMicroelectronics PREFERRED SALESTYPE
- NPN TRANSISTOR
- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED
- FULLY CHARACTERISED AT 125°C
- LARGE RBSOA

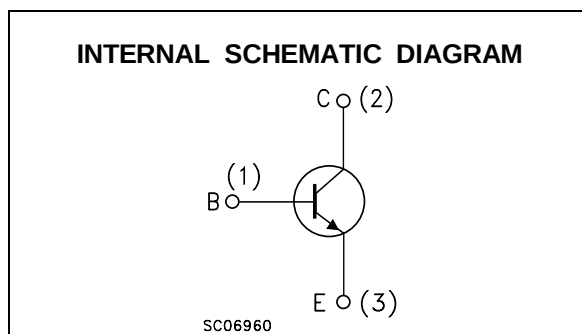
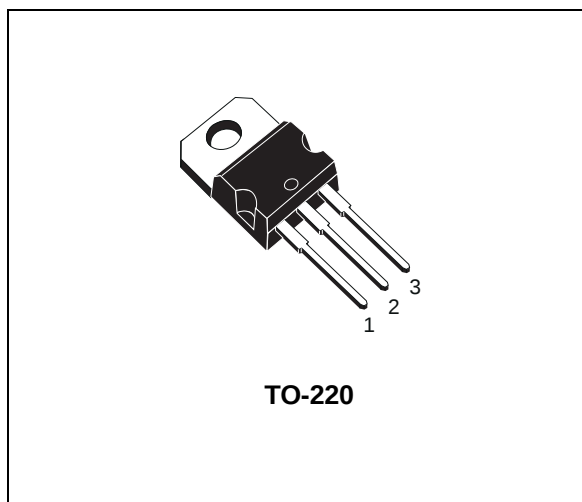
### APPLICATIONS

- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING
- FLYBACK AND FORWARD SINGLE TRANSISTOR LOW POWER CONVERTERS

### DESCRIPTION

The device is manufactured using high voltage Multi Epitaxial Planar technology for high switching speeds and high voltage capability. It uses a Cellular Emitter structure with planar edge termination to enhance switching speeds while maintaining a wide RBSOA.

The BUL series is designed for use in lighting applications and low cost switch-mode power supplies.



### ABSOLUTE MAXIMUM RATINGS

| Symbol    | Parameter                                  | Value      | Unit |
|-----------|--------------------------------------------|------------|------|
| $V_{CES}$ | Collector-Emitter Voltage ( $V_{BE} = 0$ ) | 1000       | V    |
| $V_{CEO}$ | Collector-Emitter Voltage ( $I_B = 0$ )    | 500        | V    |
| $V_{EBO}$ | Emitter-Base Voltage ( $I_C = 0$ )         | 9          | V    |
| $I_C$     | Collector Current                          | 5          | A    |
| $I_{CM}$  | Collector Peak Current ( $t_p < 5$ ms)     | 10         | A    |
| $I_B$     | Base Current                               | 3          | A    |
| $I_{BM}$  | Base Peak Current ( $t_p < 5$ ms)          | 4          | A    |
| $P_{tot}$ | Total Dissipation at $T_c = 25$ °C         | 75         | W    |
| $T_{stg}$ | Storage Temperature                        | -65 to 150 | °C   |
| $T_j$     | Max. Operating Junction Temperature        | 150        | °C   |

## THERMAL DATA

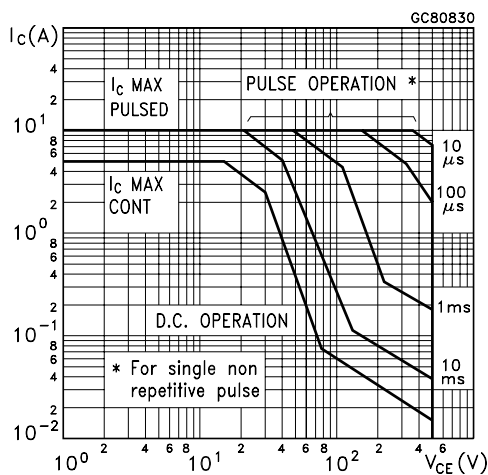
|                       |                                     |     |      |      |
|-----------------------|-------------------------------------|-----|------|------|
| R <sub>thj-case</sub> | Thermal Resistance Junction-Case    | Max | 1.65 | °C/W |
| R <sub>thj-amb</sub>  | Thermal Resistance Junction-Ambient | Max | 62.5 | °C/W |

ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

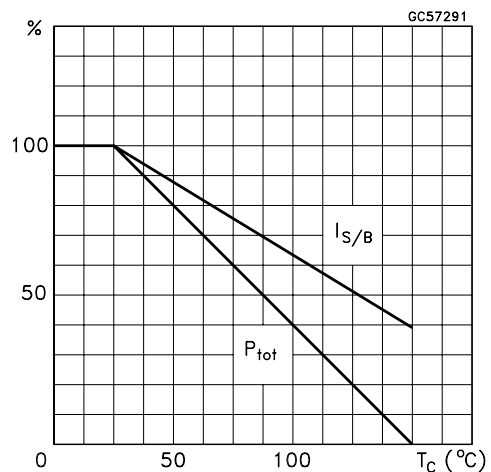
| Symbol                           | Parameter                                                 | Test Conditions                                                                                                                                                                  | Min.    | Typ.       | Max.              | Unit        |
|----------------------------------|-----------------------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------|------------|-------------------|-------------|
| I <sub>CES</sub>                 | Collector Cut-off Current (V <sub>BE</sub> = 0)           | V <sub>CE</sub> = 1000 V<br>V <sub>CE</sub> = 1000 V T <sub>j</sub> = 125 °C                                                                                                     |         |            | 100<br>500        | μA<br>μA    |
| I <sub>CEO</sub>                 | Collector Cut-off Current (I <sub>B</sub> = 0)            | V <sub>CE</sub> = 500 V                                                                                                                                                          |         |            | 250               | μA          |
| V <sub>CEO(sus)*</sub>           | Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0) | I <sub>C</sub> = 100 mA L = 25 mH                                                                                                                                                | 500     |            |                   | V           |
| V <sub>EBO</sub>                 | Emitter-Base Voltage (I <sub>C</sub> = 0)                 | I <sub>E</sub> = 10 mA                                                                                                                                                           | 9       |            |                   | V           |
| V <sub>CE(sat)*</sub>            | Collector-Emitter Saturation Voltage                      | I <sub>C</sub> = 1 A I <sub>B</sub> = 0.2 A<br>I <sub>C</sub> = 2 A I <sub>B</sub> = 0.4 A<br>I <sub>C</sub> = 3 A I <sub>B</sub> = 0.6 A                                        |         |            | 0.5<br>0.7<br>1.1 | V<br>V<br>V |
| V <sub>BE(sat)*</sub>            | Base-Emitter Saturation Voltage                           | I <sub>C</sub> = 1 A I <sub>B</sub> = 0.2 A<br>I <sub>C</sub> = 2 A I <sub>B</sub> = 0.4 A<br>I <sub>C</sub> = 3 A I <sub>B</sub> = 0.6 A                                        |         |            | 1<br>1.1<br>1.2   | V<br>V<br>V |
| h <sub>FE</sub> *                | DC Current Gain                                           | I <sub>C</sub> = 10 mA V <sub>CE</sub> = 5 V<br>I <sub>C</sub> = 3 A V <sub>CE</sub> = 2.5 V                                                                                     | 10<br>6 | 10         | 14                |             |
| t <sub>s</sub><br>t <sub>f</sub> | INDUCTIVE LOAD<br>Storage Time<br>Fall Time               | I <sub>C</sub> = 2 A I <sub>B1</sub> = 0.4 A<br>V <sub>BE(off)</sub> = -5 V R <sub>BB</sub> = 0 Ω<br>V <sub>CL</sub> = 250 V L = 200 μH<br>(see figure 1)                        |         | 1.2<br>80  | 1.9<br>160        | μs<br>ns    |
| t <sub>s</sub><br>t <sub>f</sub> | INDUCTIVE LOAD<br>Storage Time<br>Fall Time               | I <sub>C</sub> = 2 A I <sub>B1</sub> = 0.4 A<br>V <sub>BE(off)</sub> = -5V R <sub>BB</sub> = 0 Ω<br>V <sub>CL</sub> = 250 V L = 200 μH<br>T <sub>j</sub> = 125 °C (see figure 1) |         | 1.8<br>150 |                   | μs<br>ns    |

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

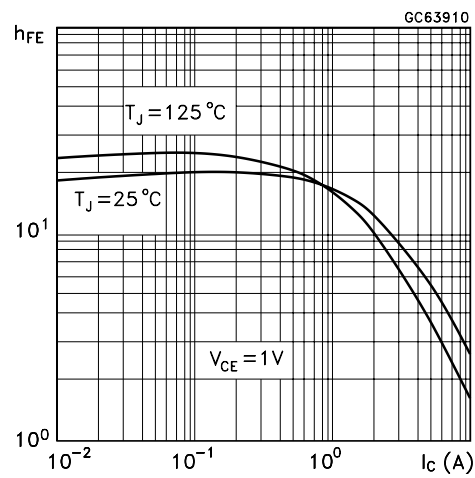
## Safe Operating Areas



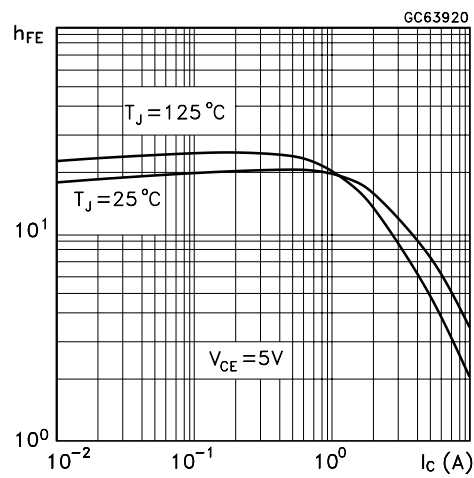
## Derating Curve



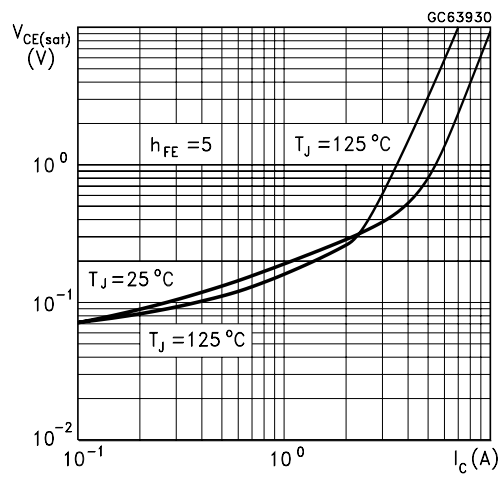
DC Current Gain



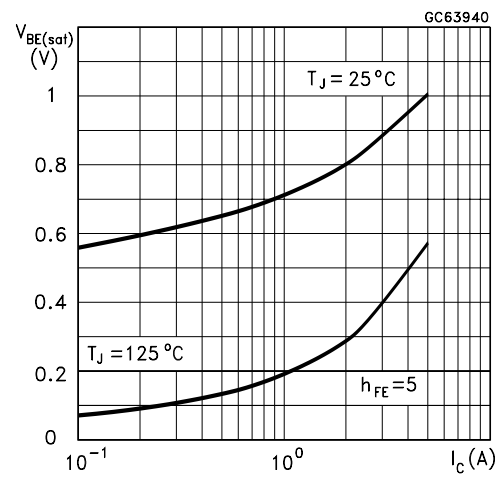
DC Current Gain



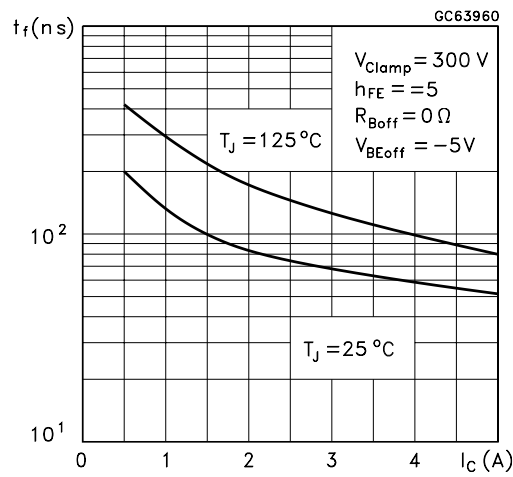
Collector Emitter Saturation Voltage



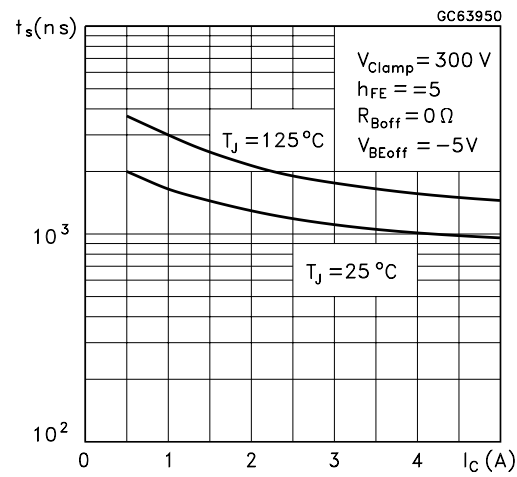
Base Emitter Saturation Voltage



Inductive Load Fall Time



Inductive Load Storage Time



Reverse Biased SOA

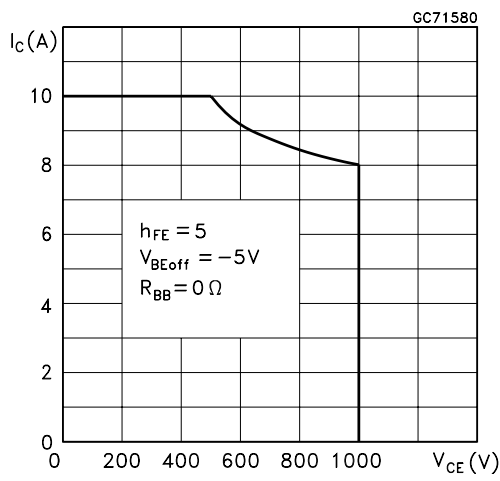
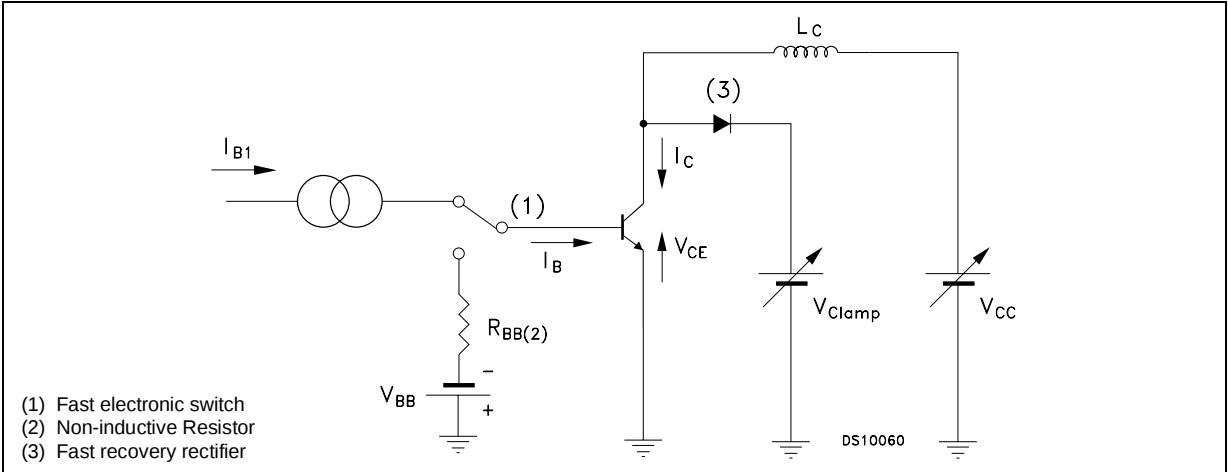


Figure 1: Inductive Load Switching Test Circuit





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